**What is claimed is:**

1. A pattern formation method for a cantilever beam shaped film by deposition using a focused ion beam device on the end of a sample comprising:

irradiating the focused ion beam and depositing a film on a narrowly limited strip shape region from ends of the sample; and

sequentially shifting the irradiation region in a tip end direction to cause a thin deposition layer to extend.

2. A pattern formation method for a bridge-shaped film by deposition using a focused ion beam device in an opening of a sample,

irradiating the focused ion beam and depositing a film on a narrowly limited strip shape region from ends of the sample; and

sequentially shifting the irradiation region in a tip end direction to cause a thin deposition layer to extend from the both ends so that the deposition layer may be joined at a central section of the opening of the sample.

3. The film pattern formation method of claim 1, wherein timing for shifting the irradiation region in a tip end direction is in time with formation of a sloping surface on a tip side of the deposition layer.

4. The film pattern forming method of claim 1, wherein a deposition layer of desired thickness is formed on the formed thin deposition layer.

5. The film pattern formation method of claim 2, wherein timing for shifting the irradiation region in a tip end direction is in time with formation of a sloping surface on a tip side of the deposition layer.

6. The film pattern forming method of claim 2, wherein a deposition layer of desired thickness is formed on the formed thin deposition layer.